

## 2<sup>nd</sup> Generation thinQ!™ SiC Schottky Diode

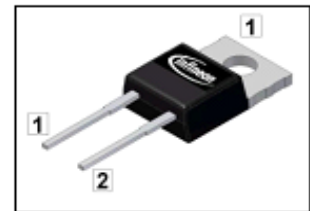
### Features

- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery/ No forward recovery
- No temperature influence on the switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Breakdown voltage tested at 5mA<sup>2)</sup>

### Product Summary

|          |     |    |
|----------|-----|----|
| $V_{DC}$ | 600 | V  |
| $Q_c$    | 24  | nC |
| $I_F$    | 10  | A  |

### PG-TO220-2



**thinQ! 2G Diode specially designed for fast switching applications like:**

- CCM PFC
- Motor Drives

| Type      | Package    | Marking | Pin 1 | Pin 2 |
|-----------|------------|---------|-------|-------|
| IDH10S60C | PG-TO220-2 | D10S60C | C     | A     |

**Maximum ratings, at  $T_J=25^\circ\text{C}$ , unless otherwise specified**

| Parameter                                                  | Symbol         | Conditions                                            | Value       | Unit             |
|------------------------------------------------------------|----------------|-------------------------------------------------------|-------------|------------------|
| Continuous forward current                                 | $I_F$          | $T_C < 140^\circ\text{C}$                             | 10          | A                |
| RMS forward current                                        | $I_{F,RMS}$    | $f=50\text{ Hz}$                                      | 15          |                  |
| Surge non-repetitive forward current, sine halfwave        | $I_{F,SM}$     | $T_C=25^\circ\text{C}, t_p=10\text{ ms}$              | 84          |                  |
| Repetitive peak forward current                            | $I_{F,RM}$     | $T_J=150^\circ\text{C}, T_C=100^\circ\text{C}, D=0.1$ | 39          |                  |
| Non-repetitive peak forward current                        | $I_{F,max}$    | $T_C=25^\circ\text{C}, t_p=10\text{ }\mu\text{s}$     | 350         |                  |
| $i^2t$ value                                               | $\int i^2 dt$  | $T_C=25^\circ\text{C}, t_p=10\text{ ms}$              | 35          | A <sup>2</sup> s |
| Repetitive peak reverse voltage                            | $V_{RRM}$      |                                                       | 600         | V                |
| Diode dv/dt ruggedness                                     | dv/dt          | $V_R = 0 \dots 480\text{V}$                           | 50          | V/ns             |
| Power dissipation                                          | $P_{tot}$      | $T_C=25^\circ\text{C}$                                | 100         | W                |
| Operating and storage temperature                          | $T_J, T_{stg}$ |                                                       | -55 ... 175 | °C               |
| Mounting torque                                            |                | M3 and M3.5 screws                                    | 60          | Mcm              |
| Soldering temperature, wavesoldering only allowed at leads | $T_{sld}$      | 1.6mm (0.063 in.) from case for 10s                   | 260         | °C               |

| Parameter                                                               | Symbol     | Conditions                                                                   | Values |      |      | Unit |
|-------------------------------------------------------------------------|------------|------------------------------------------------------------------------------|--------|------|------|------|
|                                                                         |            |                                                                              | min.   | typ. | max. |      |
| Thermal characteristics                                                 |            |                                                                              |        |      |      |      |
| Thermal resistance, junction - case                                     | $R_{thJC}$ |                                                                              | -      | -    | 1.5  | K/W  |
| Thermal resistance, junction - ambient                                  | $R_{thJA}$ | leaded                                                                       | -      | -    | 62   |      |
| Electrical characteristics, at $T_j$ =25 °C, unless otherwise specified |            |                                                                              |        |      |      |      |
| Static characteristics                                                  |            |                                                                              |        |      |      |      |
| DC blocking voltage                                                     | $V_{DC}$   | $I_R$ =0.14 mA                                                               | 600    | -    | -    | V    |
| Diode forward voltage                                                   | $V_F$      | $I_F$ =10 A, $T_j$ =25 °C                                                    | -      | 1.5  | 1.7  |      |
|                                                                         |            | $I_F$ =10 A, $T_j$ =150 °C                                                   | -      | 1.7  | 2.1  |      |
| Reverse current                                                         | $I_R$      | $V_R$ =600 V, $T_j$ =25 °C                                                   | -      | 1.4  | 140  | µA   |
|                                                                         |            | $V_R$ =600 V, $T_j$ =150 °C                                                  | -      | 5    | 1400 |      |
| AC characteristics                                                      |            |                                                                              |        |      |      |      |
| Total capacitive charge                                                 | $Q_c$      | $V_R$ =400 V, $I_F$ ≤ $I_{F,max}$ ,<br>$di_F/dt$ =200 A/µs,<br>$T_j$ =150 °C | -      | 24   | -    | nC   |
| Switching time <sup>3)</sup>                                            | $t_c$      |                                                                              | -      | -    | <10  | ns   |
| Total capacitance                                                       | C          | $V_R$ =1 V, $f$ =1 MHz                                                       | -      | 480  | -    | pF   |
|                                                                         |            | $V_R$ =300 V, $f$ =1 MHz                                                     | -      | 60   | -    |      |
|                                                                         |            | $V_R$ =600 V, $f$ =1 MHz                                                     | -      | 60   | -    |      |

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> All devices tested under avalanche conditions, for a time periode of 5ms, at 5mA.

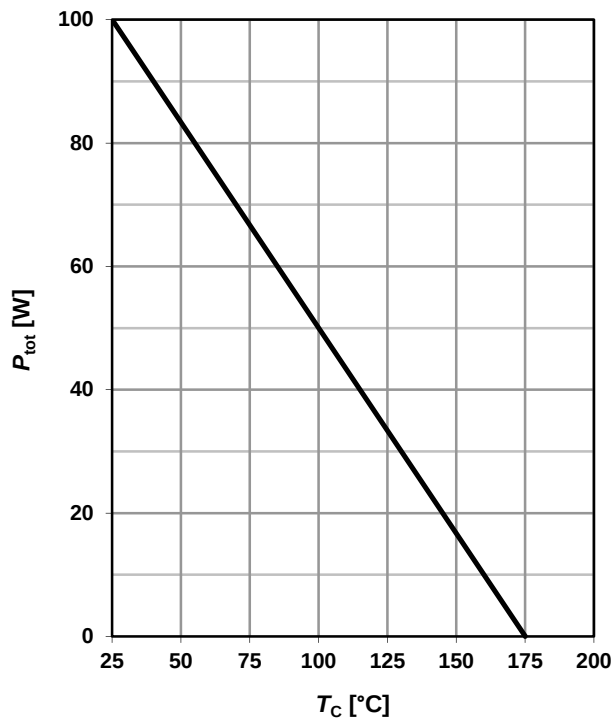
<sup>3)</sup>  $t_c$  is the time constant for the capacitive displacement current waveform (independent from  $T_j$ ,  $I_{LOAD}$  and  $di/dt$ ), different from  $t_{rr}$ , which is dependent on  $T_j$ ,  $I_{LOAD}$ ,  $di/dt$ . No reverse recovery time constant  $t_{rr}$  due to absence of minority carrier injection.

<sup>4)</sup> Only capacitive charge occuring, guaranteed by design.

### 1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$

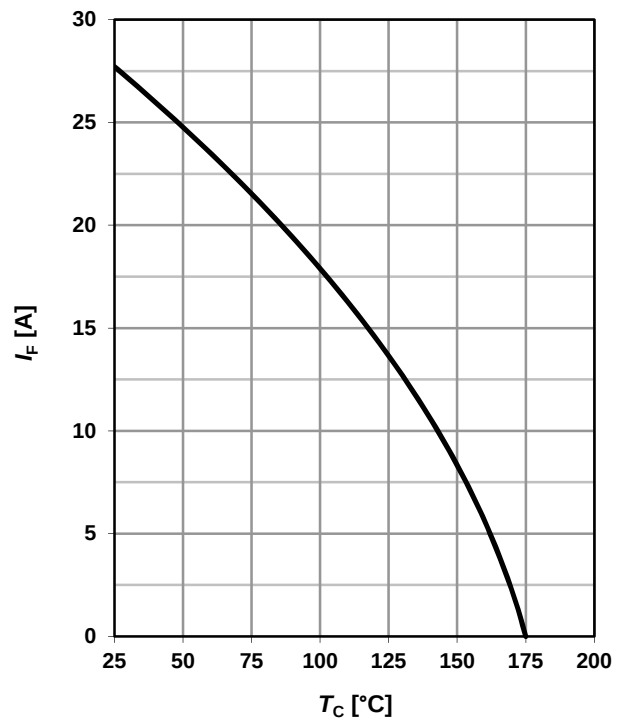
parameter:  $R_{\text{thJC(max)}}$



### 2 Diode forward current

$$I_F = f(T_C); T_j \leq 175 \text{ °C}$$

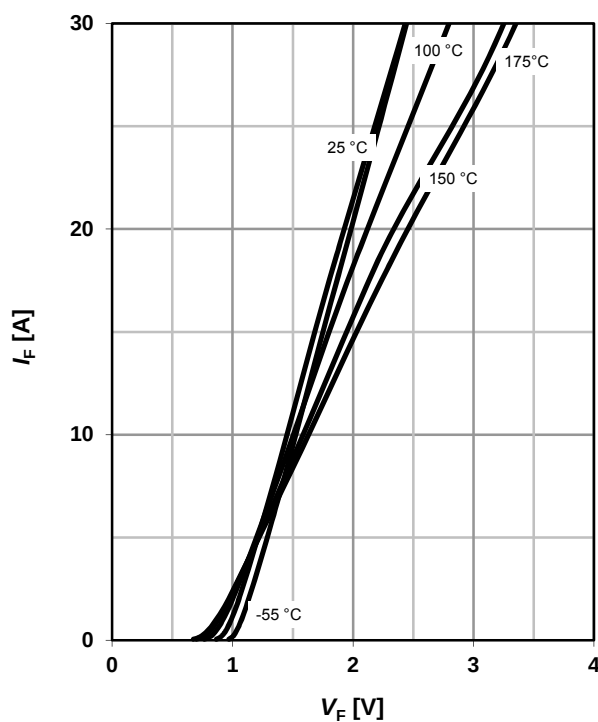
parameter:  $R_{\text{thJC(max)}}$ ;  $V_{F(\text{max})}$



### 3 Typ. forward characteristic

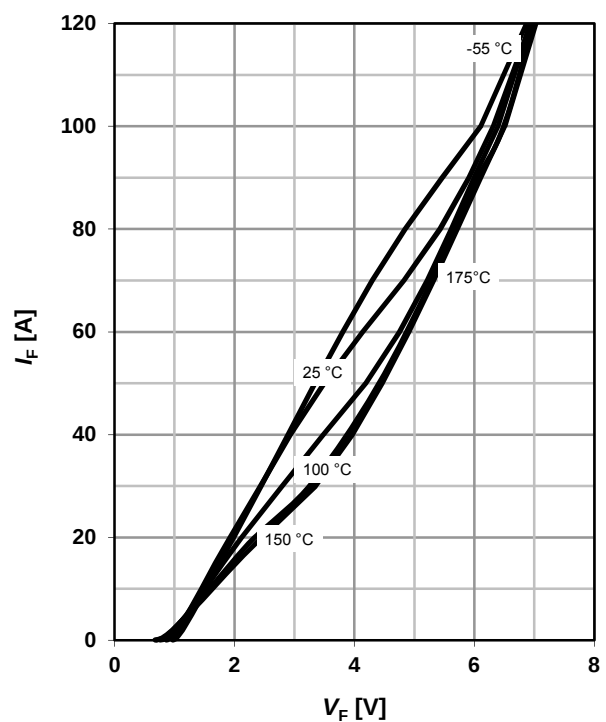
$$I_F = f(V_F); t_p = 400 \text{ } \mu\text{s}$$

parameter:  $T_j$



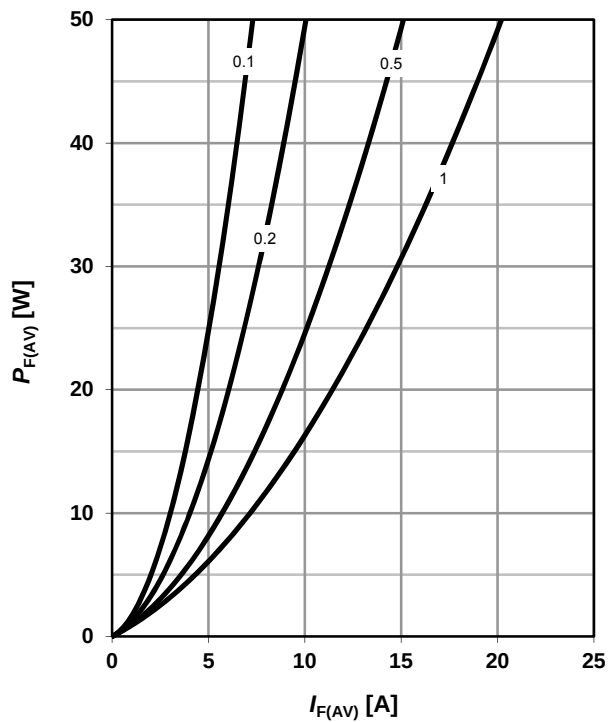
### 4 Typ. forward characteristic in surge current mode

$$I_F = f(V_F); t_p = 400 \text{ } \mu\text{s}; \text{ parameter: } T_j$$



### 5 Typ. forward power dissipation vs. average forward current

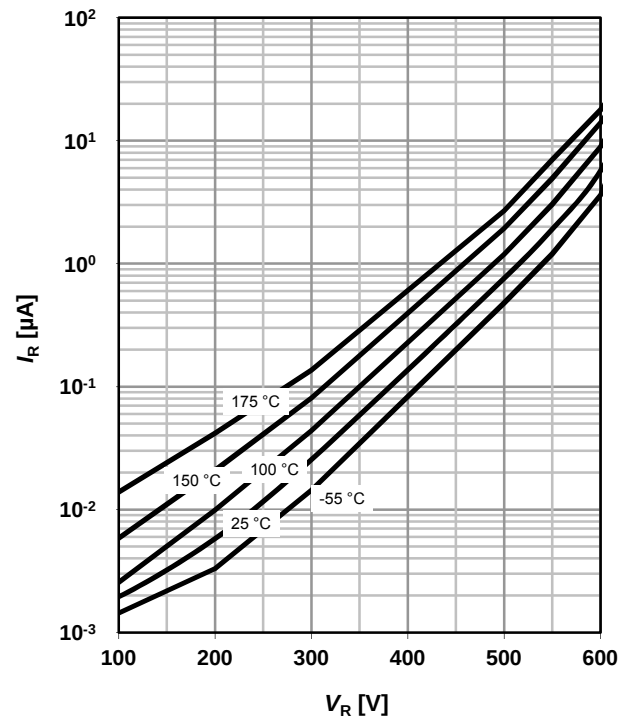
$P_{F(AV)} = f(I_{F(AV)})$ ,  $T_C = 100^\circ\text{C}$ , parameter:  $D = t_p/T$



### 6 Typ. reverse current vs. reverse voltage

$I_R = f(V_R)$

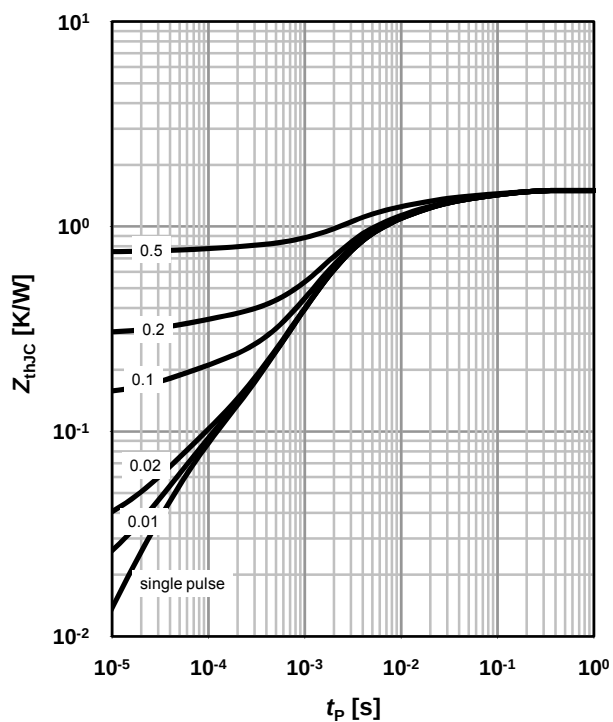
parameter:  $T_j$



### 7 Transient thermal impedance

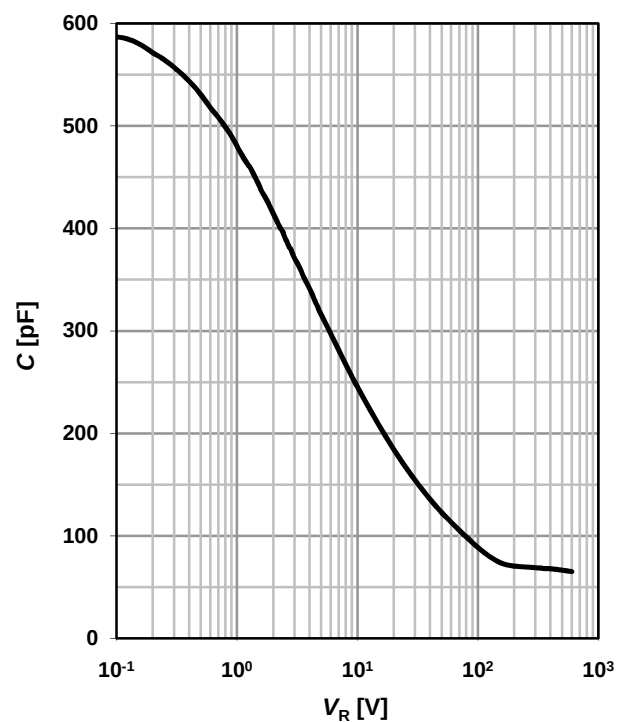
$Z_{thJC} = f(t_p)$

parameter:  $D = t_p/T$



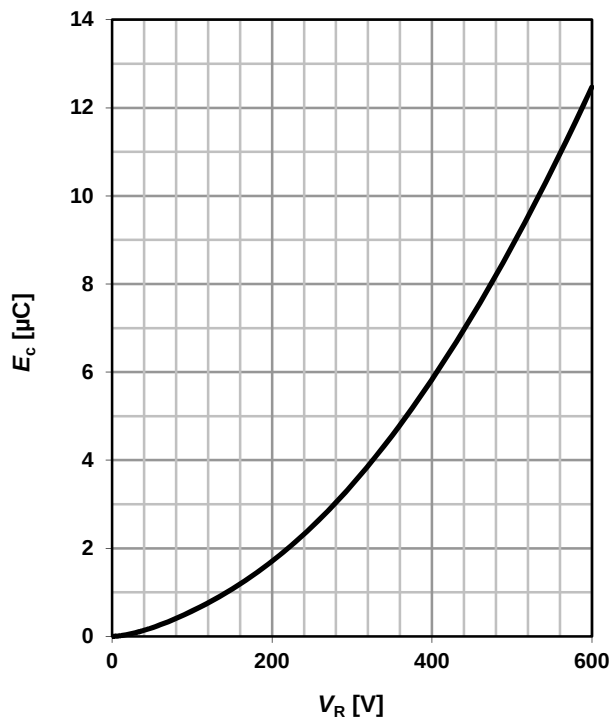
### 8 Typ. capacitance vs. reverse voltage

$C = f(V_R)$ ;  $T_C = 25^\circ\text{C}$ ,  $f = 1\text{ MHz}$



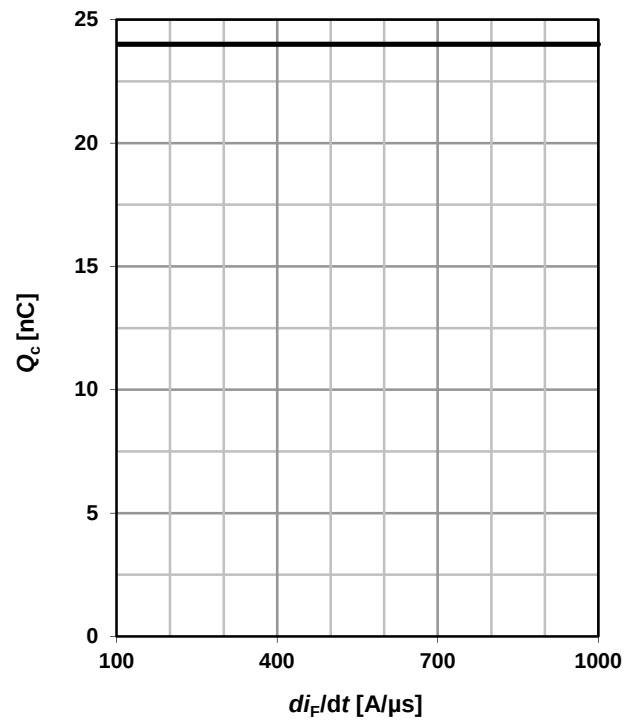
### 9 Typ. C stored energy

$$E_C = f(V_R)$$

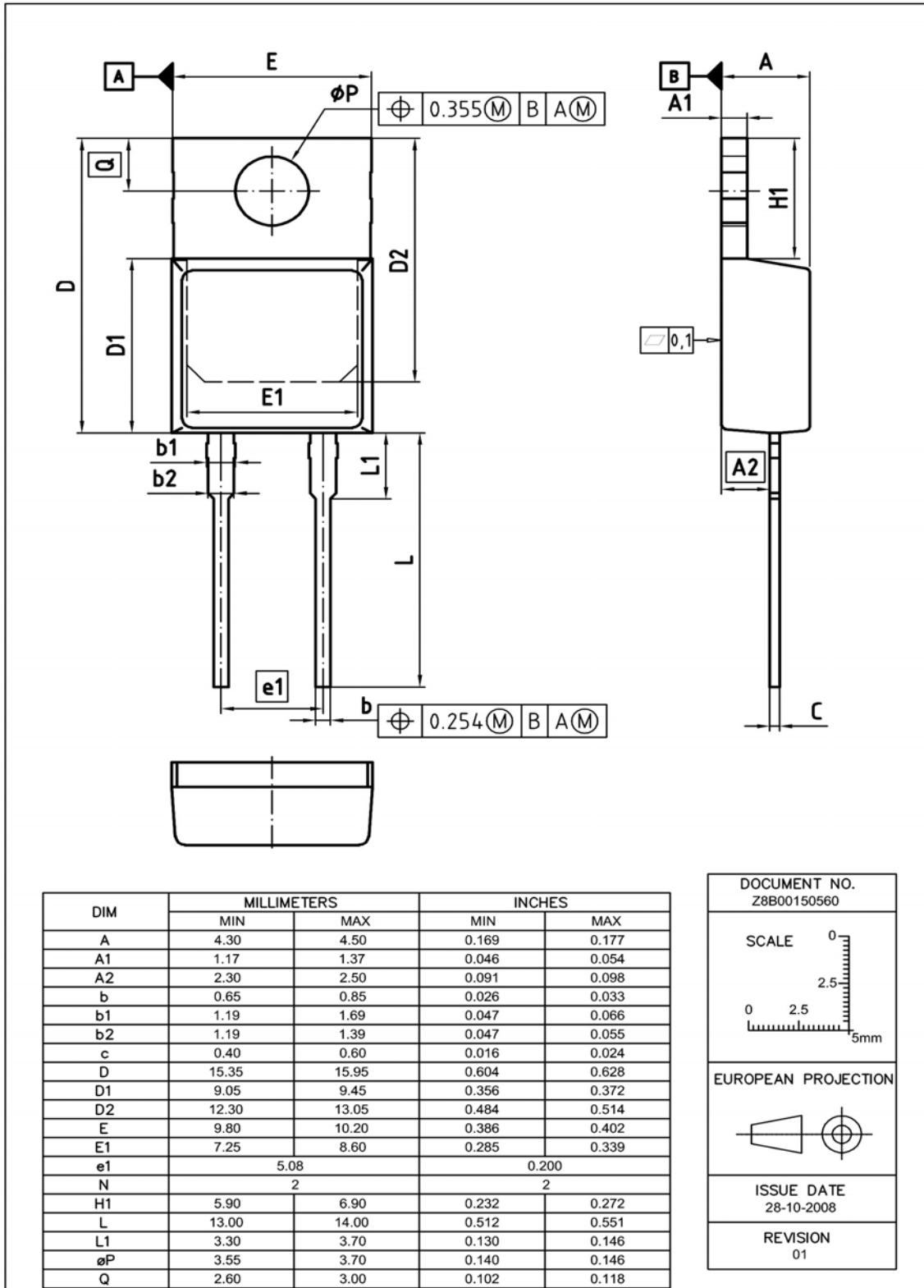


### 10 Typ. Capacitive charge vs. current slope

$$Q_C = f(di_F/dt)^{4/3}; T_j = 150^\circ\text{C}; I_F \leq I_{F,\text{max}}$$



## PG-TO220-2: Outline



Dimensions in mm/inches

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